

AMENDMENTS TO THE CLAIMS

Claims 1-13 (Cancelled).

14. (Currently Amended) A method of forming a semiconductor device, the method comprising the steps of:

forming a layer of insulation material over a semiconductor substrate, the layer of insulation material having a top surface;

etching the layer of insulation material to form a plurality of ~~first~~ trenches in the layer of insulation material, the top surface of the layer of insulation material having a trench region that lies between adjacent trenches, each ~~first~~ trench having a ~~first~~ bottom surface vertically spaced a first distance apart from the top surface; and

etching the layer of insulation material and the plurality of ~~first~~ trenches to ~~form a second trench in the layer of insulation material, the second trench having a plurality of second bottom surfaces vertically spaced a second distance apart from the top surface, and third bottom surfaces vertically spaced a third distance apart from the top surface, the third bottom surfaces lying below the second bottom surfaces~~ lower the top surface of the layer of insulation material in the trench region to form a trench surface that lies below and parallel to the top surface, and to lower the bottom surface of each trench such that each bottom surface is vertically spaced a second distance apart from the top surface, the second distance being greater than the first distance.

15. (Currently Amended) The method of claim 14 wherein the ~~second etching step~~ of etching the layer of insulation material and the plurality of trenches includes the steps of:

forming a layer of masking material on the layer of insulation material;

patterning the layer of masking material to expose a portion of the top surface of the layer of insulation material and the plurality of first trenches; and anisotropically etching the layer of insulation material and the plurality of first trenches ~~to form the second trench.~~

16. (Currently Amended) The method of claim 14 and further comprising the steps of:

forming a layer of conductive material on the layer of insulation material ~~to fill up the second trench,~~ the layer of conductive material filling up the trenches; and

planarizing the layer of conductive material to form a conductive region, the conductive region having a top surface that is substantially planar with the top surface of the layer of insulation material, the conductive region in the trenches forming a plurality of bottom fingers with bottom surfaces that lie parallel to the top surface of the layer of insulation material.

17. (Currently Amended) The method of claim 16 wherein the conductive region is formed to have a number of loops that lie substantially in a same plane, the loops being electrically connected together.

18. (Currently Amended) The method of claim 16 wherein ~~the conductive region is connected to a contact~~ a top surface of a single contact is directly connected to the bottom surfaces of the plurality of bottom fingers.

19. (Currently Amended) The method of claim 16 wherein ~~the conductive region is connected to a via~~ a top surface of a single via is directly connected to the bottom surfaces of the plurality of bottom fingers.

20. (Previously Presented) The method of claim 16 wherein the layer of conductive material includes:

a layer of barrier material formed on the layer of insulation material;
a layer of seed material formed on the layer of barrier material; and
a layer of copper formed on the layer of seed material.

21. (Cancelled).

22. (Currently Amended) ~~The method of claim 21 and further comprising the step of~~ A method of forming a semiconductor device, the method comprising the steps of:

forming a layer of insulation material over a semiconductor substrate, the layer of insulation material having a top surface;

etching the layer of insulation material to form a first trench in the layer of insulation material, the first trench having a first bottom surface vertically spaced a first distance apart from the top surface; and

etching the layer of insulation material and the first trench to form a second trench in the layer of insulation material, the second trench having a second bottom surface vertically spaced a second distance apart from the top surface, and a third bottom surface vertically spaced a third distance apart from the top surface, the third bottom surface lying below the second bottom surface distance being greater than the first distance, the third distance being greater than the second distance.

23. (Currently Amended) The method of claim 22 and further comprising the steps of:

forming a layer of conductive material on the layer of insulation material to fill up the second trench; and

planarizing the layer of conductive material to form a conductive region, the conductive region having a top surface that is substantially planar with the top surface of the layer of insulation material, the conductive region contacting the third bottom surface forming a bottom finger surface that lies parallel to the top surface of the layer of insulation material.

24. (Previously Presented) The method of claim 23 wherein the second etching step includes the steps of:

forming a layer of masking material on the layer of insulation material;
patterning the layer of masking material to expose the first trench and a portion of the top surface of the layer of insulation material;
anisotropically etching the layer of insulation material and the first trench to form the second trench.

25. (Previously Presented) The method of claim 23 wherein the conductive region is formed to have a number of loops.

26. (Currently Amended) The method of claim 25 wherein the loops lie substantially in a same plane, the loops being electrically connected together.

27. (Currently Amended) The method of claim 23 wherein the ~~conductive region is connected to a contact~~ a top surface of a single contact is directly connected to the bottom finger surface.

28. (Currently Amended) The method of claim 23 wherein the ~~conductive region is connected to a via~~ a top surface of a single via is directly connected to the bottom finger surface.

29. (Previously Presented) The method of claim 23 wherein the layer of conductive material includes:

- a layer of barrier material formed on the layer of insulation material;
- a layer of seed material formed on the layer of barrier material; and
- a layer of copper formed on the layer of seed material.